Amendments to the Claims

Claims 1- 54 (cancelled)

Claim 55 (new): A method of forming a conductive material, comprising:

providing a semiconductor substrate;

forming a first conductive material over the substrate, the first conductive material comprising one or more of TiN, WN, TaN, elemental Ta, elemental Ti and elemental W; and

depositing a second conductive material physically against the first conductive material, the second conductive material consisting essentially of a metal and being different than the first conductive material, wherein the depositing comprises:

providing a metallo-organic precursor proximate the first conductive material, wherein the metallo-organic precursor comprises the metal and carbon; and

exposing the precursor to a reducing atmosphere to release the metal from the precursor to form the second conductive material physically against the first conductive material without an insulative composition between the first and second conductive materials.

Claim 56 (new): The method of claim 55 further comprising forming an insulative material over the substrate, wherein the insulative material comprises sidewalls defining an opening extending to the substrate in at least one cross-section, and wherein the forming the first conductive material comprises forming the first conductive material within the opening.

Claim 57 (new): The method of claim 56 further comprising etching the second conductive material into a rectangular block, wherein the block comprises a sidewall aligned vertically with one of the sidewalls of the insulative material in at least the one cross-section.

Claim 58 (new): The method of claim 56 further comprising etching the second conductive material into a rectangular block, wherein the sidewalls of the block are aligned vertically over the opening in at least the one cross-section.

Claim 59 (new): The method of claim 55 wherein:

the metallo-organic precursor consists essentially of tricarbonyl-cyclohexadiene ruthenium;

the reducing atmosphere consists essentially of ammonia; and

the second conductive material has a thickness of about 450 Å.

Claim 60 (new): A method of forming a conductive material, comprising:

providing a semiconductor substrate having tungsten-comprising layer thereover;

exposing one or more metallo-organic precursors to a reducing atmosphere to release metal from at least one of said precursors; and

depositing the released metal over the tungsten-comprising layer to form a conductive material on the tungsten-comprising layer.

Claim 61 (new): The method of claim 60 wherein the tungsten-comprising layer comprises an upper surface of elemental tungsten.

Claim 62 (new): The method of claim 61 wherein the conductive material is formed physically against the upper surface.

Claim 63 (new): The method of claim 60 wherein the one or more precursors comprise one or more of ruthenium, rhodium, iridium, cobalt, palladium, and nickel.

Claim 64 (new): The method of claim 63 wherein tricarbonyl-cyclohexadiene ruthenium is comprised by said one or more precursors.

Claim 65 (new): The method of claim 60 wherein the reducing atmosphere comprises ammonia.

Claim 66 (new): A method of forming a conductive material, comprising:

providing a semiconductor substrate;

exposing one or more metallo-organic precursors to a reducing atmosphere to release metal from at least one of said precursors, wherein said one or more precursors comprise carbon and one or more of Co, Pd, and Ni; and

depositing the released metal over the semiconductor substrate to form a conductive material on the semiconductor substrate.

Claim 67 (new): The method of claim 66 wherein the substrate comprises an oxidizable upper surface.

Claim 68 (new): The method of claim 66 wherein the substrate comprises an oxidizable upper surface and wherein the conductive material is formed physically against the upper surface.

Claim 69 (new): The method of claim 66 wherein the reducing atmosphere comprises H_2.